

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC4215

HIGH FREQUENCY AMPLIFIER APPLICATIONS

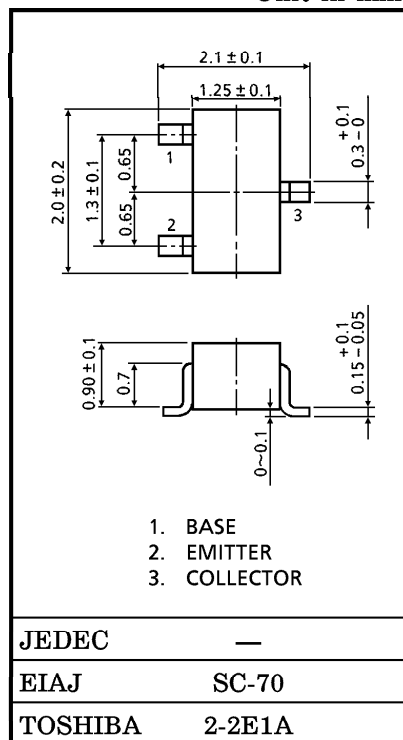
FM, RF, MIX, IF AMPLIFIER APPLICATIONS

- Small Reverse Transfer Capacitance : $C_{re} = 0.55\text{pF}$ (Typ.)
- Low Noise Figure : $NF = 2\text{dB}$ (Typ.) ($f = 100\text{MHz}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

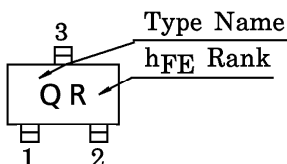
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Base Current	I_B	4	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~125	$^\circ\text{C}$

Unit in mm



Weight : 0.006g

Marking



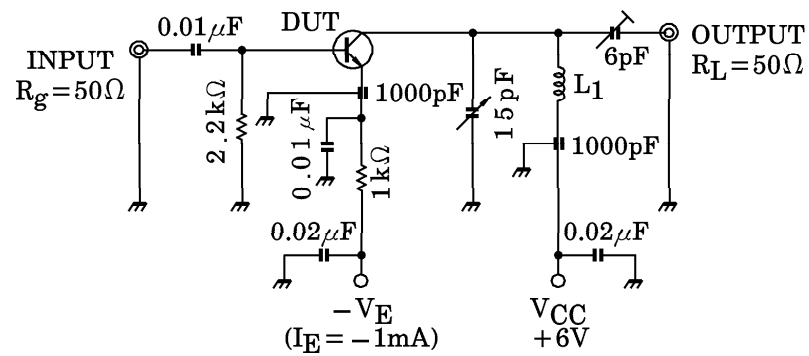
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$	—	—	0.5	μA
DC Current Gain	h_{FE} (Note)	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	40	—	200	—
Reverse Transfer Capacitance	C_{re}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	—	0.55	—	pF
Transition Frequency	f_T	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	260	550	—	MHz
Collector-Base Time Constant	$C_{c-rbb'}$	$V_{CE} = 6\text{V}, I_E = -1\text{mA}, f = 30\text{MHz}$	—	—	25	ps
Noise Figure	NF	$V_{CC} = 6\text{V}, I_E = -1\text{mA}, f = 100\text{MHz}, \text{Fig.1}$	—	2	5.0	dB
Power Gain	G_{pe}		17	23	—	dB

(Note) h_{FE} Classification R : 40~80, O : 70~140, Y : 120~240

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L₁ : 0.8mmφ SILVER PLATED COPPER WIRE, 4T, 10mm ID, 8mm LENGTH

Fig.1 NF, G_{pe} TEST CIRCUIT

